

BUK753R4-30B

N-channel TrenchMOS standard level FET

Rev. 2 — 21 April 2011 **Product data sheet**

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	30	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see Figure 1; see Figure 3	[1]	-	-	75	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2		-	-	255	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 12; see Figure 13		-	2.9	3.4	mΩ

Table 1. Quick reference data *...continued*

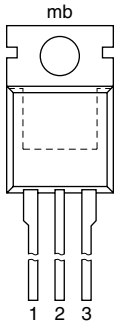
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \leq$ 30 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	1.3	J
Dynamic characteristics						
Q_{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 24 V; V_{GS} = 10 V; see Figure 14	-	23	-	nC

[1] Continuous current is limited by package.

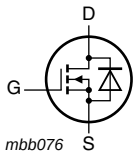
2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		



SOT78A (TO-220AB)



3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK753R4-30B	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	30	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1; see Figure 3	[1][2]	-	198	A
			[3]	-	75	A
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1	[3]	-	75	A
I_{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \leq 10$ µs; see Figure 3		-	794	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2		-	255	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1][2]	-	198	A
			[3]	-	75	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C		-	794	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \leq 30$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	1.3	J
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		[4][5]	-	-	J

[1] Current is limited by power dissipation chip rating.

[2] Refer to document 9397 750 12572 for further information.

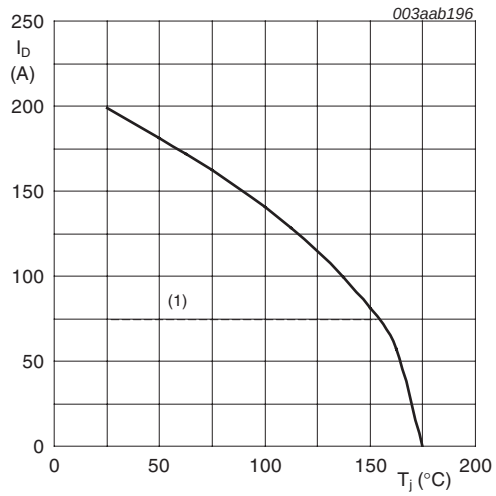
[3] Continuous current is limited by package.

[4] Max value not quoted; Single-shot avalanche rating limited by T_j(max) of 175 °C.

[5] Repetitive avalanche rating limited by an average T_j of 170 °C; Refer to application note AN10273 for further information.

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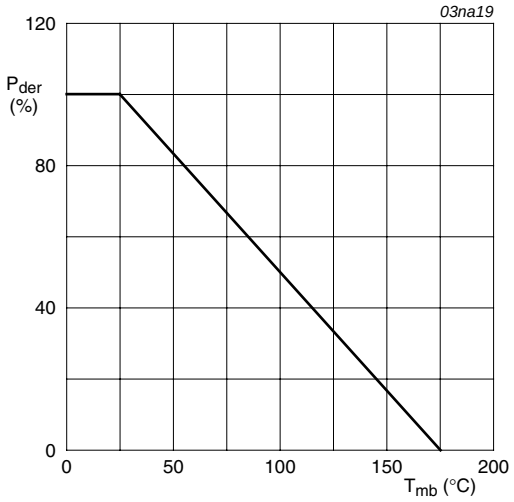
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$V_{GS} \geq 5\ V$

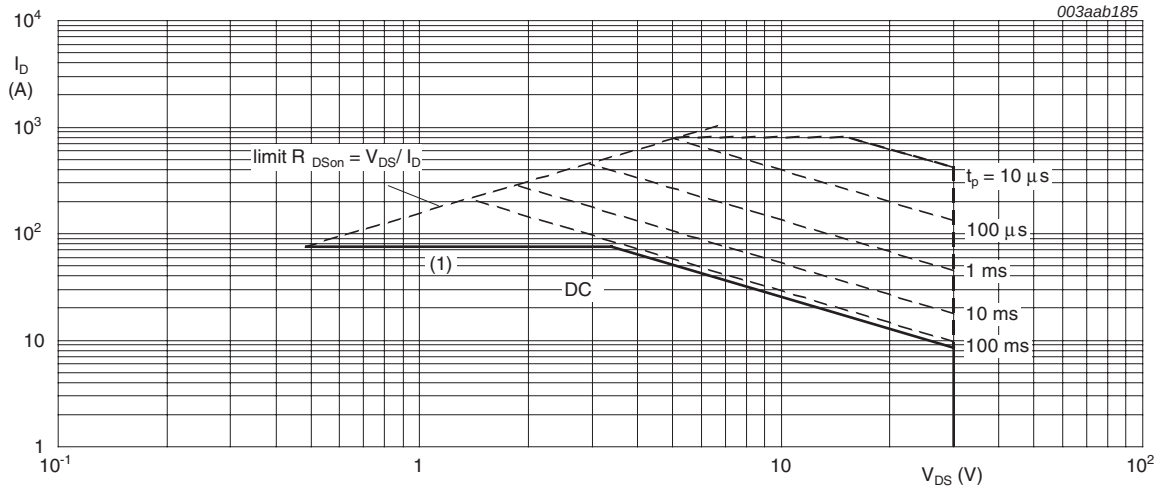
(1) Capped at 75 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25\ °C; I_{DM}$ is single pulse

(1) Capped at 75 A due to package.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.59	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

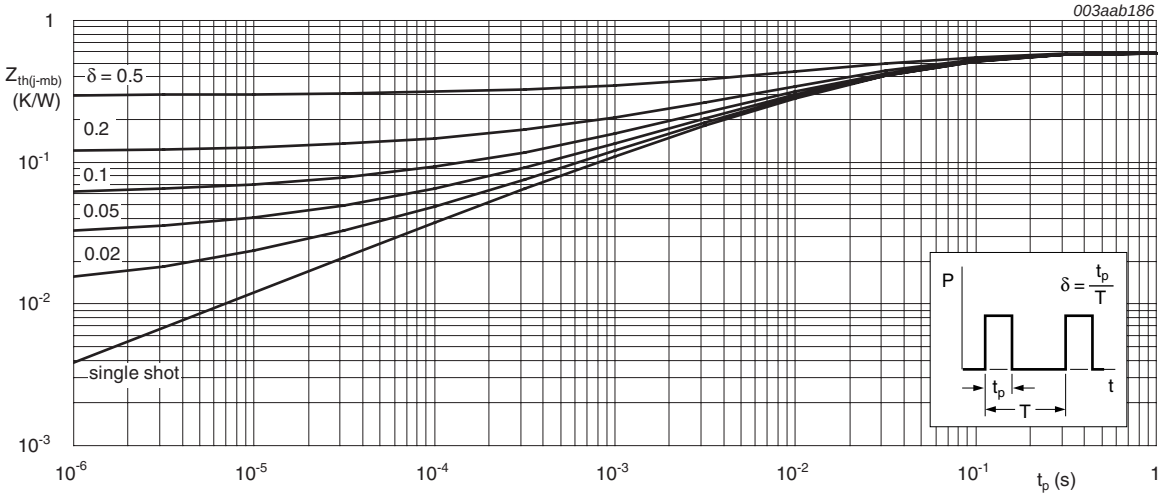


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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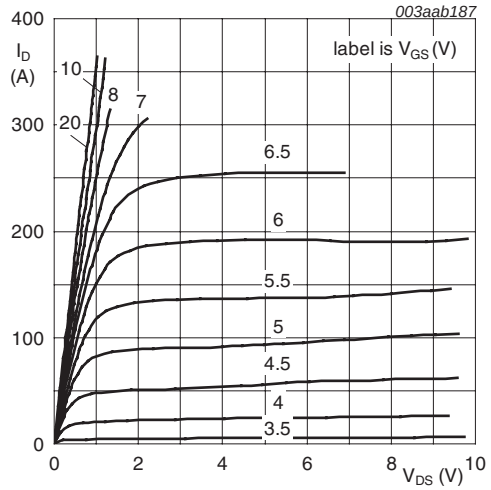
6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	27	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 10; see Figure 11	2	3	4	V
V_{GSth}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 10; see Figure 11	-	-	4.4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 10; see Figure 11	1	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 12; see Figure 13	-	2.9	3.4	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 12; see Figure 13	-	-	6.5	mΩ
I_{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 24 V; V_{GS} = 10 V; see Figure 14	-	75	-	nC
Q_{GS}	gate-source charge		-	19	-	nC
Q_{GD}	gate-drain charge		-	23	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; see Figure 15	-	3713	4951	pF
C_{oss}	output capacitance		-	1249	1499	pF
C_{rss}	reverse transfer capacitance		-	460	630	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω	-	32	-	ns
t_r	rise time		-	64	-	ns
$t_{d(off)}$	turn-off delay time		-	89	-	ns
t_f	fall time		-	71	-	ns
L_D	internal drain inductance	from contact screw on mounting base to centre of die	-	3.5	-	nH
		from drain lead 6 mm from package to centre of die	-	4.5	-	nH
L_S	internal source inductance	from source lead to source bond pad	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 16	-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 30 V	-	70	-	ns
Q_r	recovered charge		-	58	-	nC

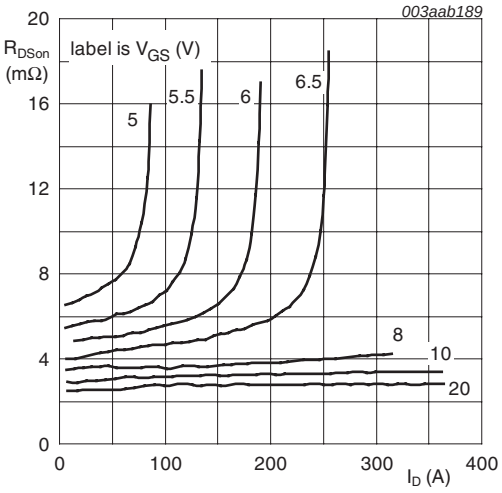
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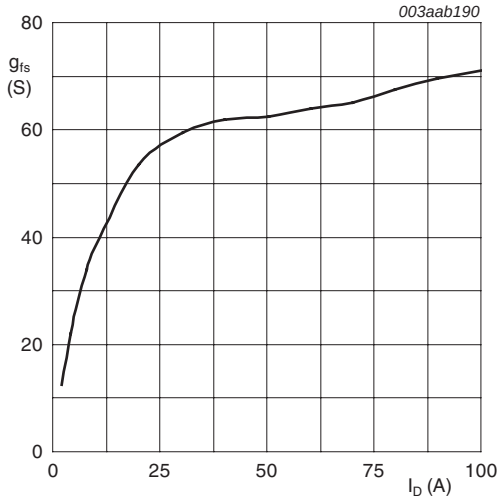
T_j = 25 °C

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



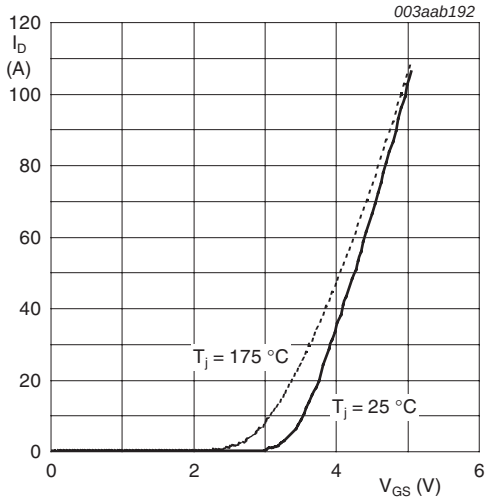
T_j = 25 °C

Fig 6. Drain-source on-state resistance as a function of drain current; typical values



T_j = 25 °C; V_{DS} = 25 V

Fig 7. Forward transconductance as a function of drain current; typical values



V_{DS} = 25 V

Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

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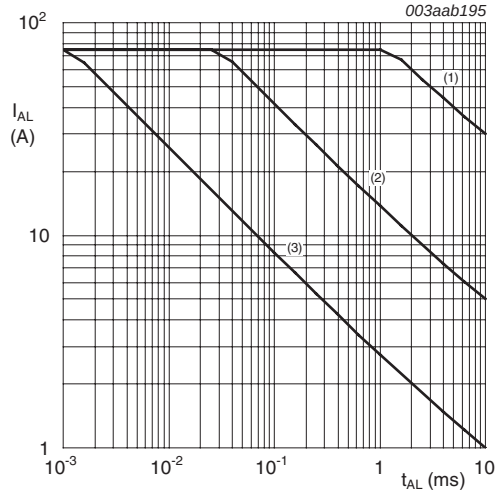
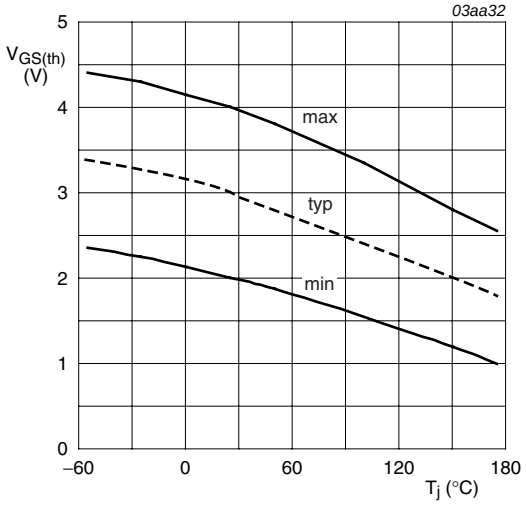
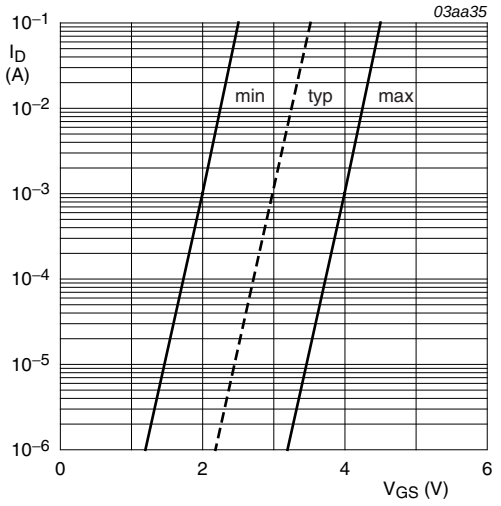


Fig 9. Single shot and repetitive avalanche rating; avalanche current as a function of avalanche time



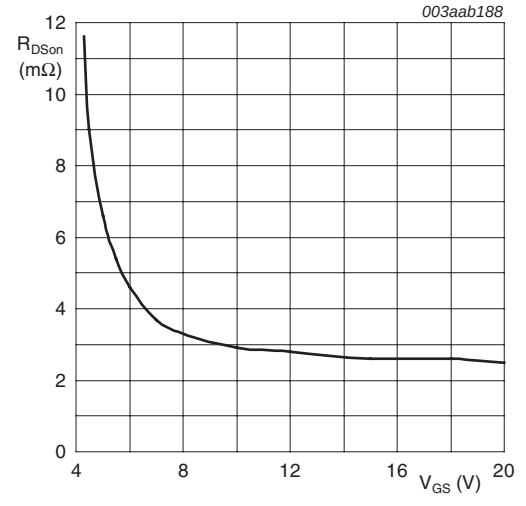
$$I_D = 1mA; V_{DS} = V_{GS}$$

Fig 10. Gate-source threshold voltage as a function of junction temperature



$$T_j = 25\,°C; V_{DS} = 5V$$

Fig 11. Sub-threshold drain current as a function of gate-source voltage

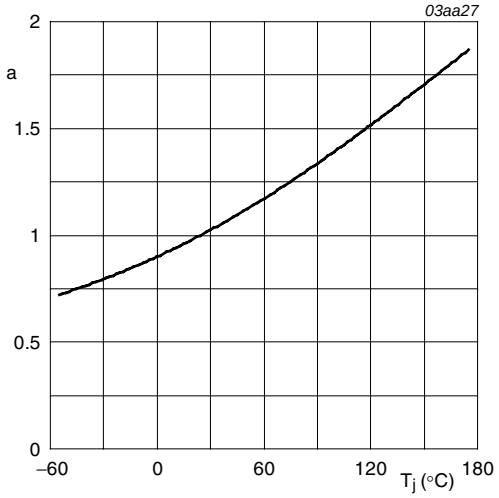


$$T_j = 25\,°C; I_D = 10\,A$$

Fig 12. Drain-source on-state resistance as a function of gate-source voltage; typical values

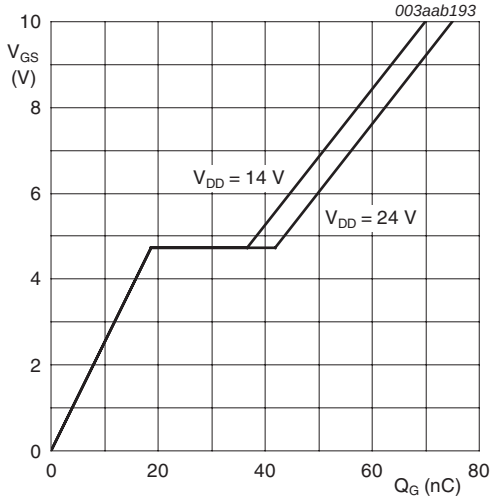
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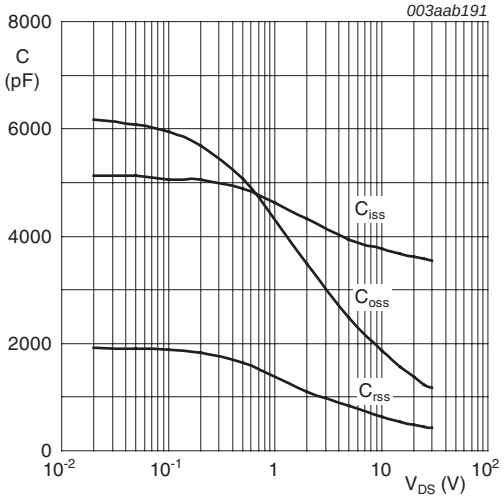
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature



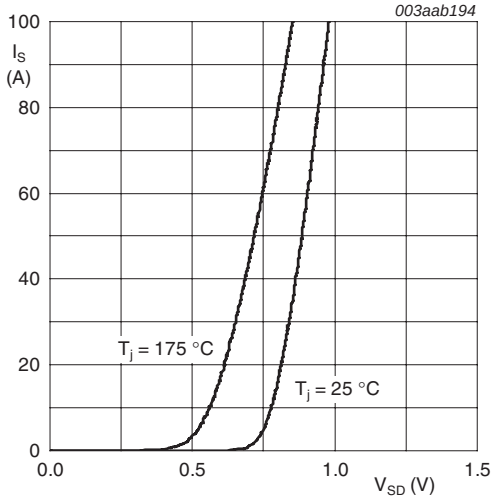
$$T_j = 25\,°C; I_D = 25A$$

Fig 14. Gate-source voltage as a function of gate charge; typical values



$$V_{GS} = 0V; f = 1MHz$$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$$V_{GS} = 0V$$

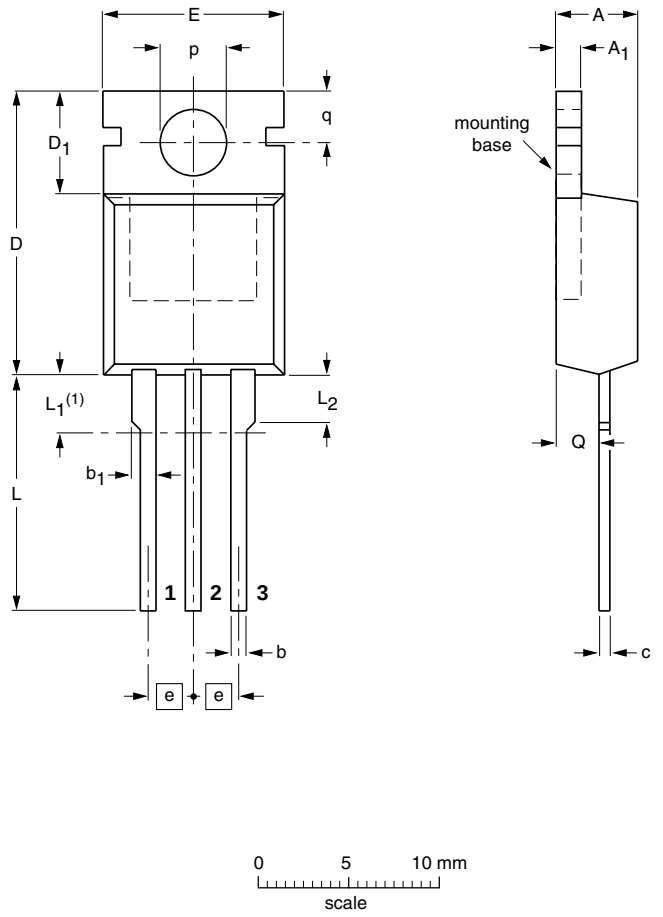
Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

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7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78A**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	c	D	D_1	E	e	L	L_1(1)	L_2 max.	p	q	Q
mm	4.5 4.1	1.39 1.27	0.9 0.6	1.3 1.0	0.7 0.4	15.8 15.2	6.4 5.9	10.3 9.7	2.54	15.0 13.5	3.30 2.79	3.0	3.8 3.6	3.0 2.7	2.6 2.2

Note

1. Terminals in this zone are not tinned.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78A		3-lead TO-220AB	SC-46			~~03-01-22~~ 05-03-14

Fig 17. Package outline SOT78A (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK753R4-30B v.2	20110421	Product data sheet	-	BUK75_763R4-30B_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Type number BUK753R4-30B separated from data sheet BUK75_763R4-30B_1.			
BUK75_763R4-30B_1	20060105	Product specification	-	-

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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10. Contact information

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11. Contents

1 Product profile 1
1.1 General description 1
1.2 Features and benefits 1
1.3 Applications 1
1.4 Quick reference data 1
2 Pinning information 2
3 Ordering information 2
4 Limiting values 3
5 Thermal characteristics 5
6 Characteristics 6
7 Package outline 10
8 Revision history 11
9 Legal information 12
9.1 Data sheet status 12
9.2 Definitions 12
9.3 Disclaimers 12
9.4 Trademarks 13
10 Contact information 13

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Date of release: 21 April 2011
Document identifier: BUK753R4-30B